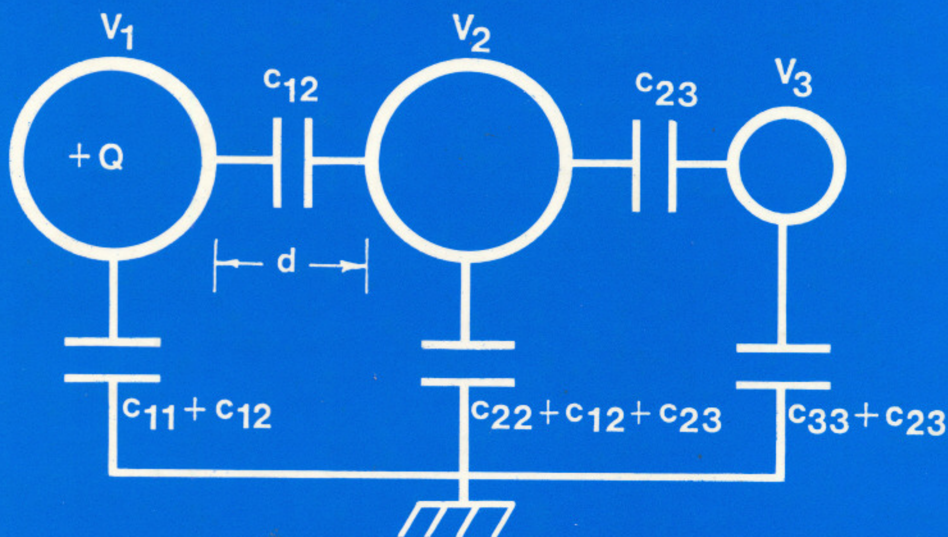
Electrostatic Damage in Electronics: Devices and Systems

William D. Greason



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